

0039-7271-2SRD

*RESPONSE UNDER 37 CFR 1.116-
EXPEDITED PROCEDURE EXAMINING
GROUP 2826

#9
Amend
B
(NE)
8.8.02
ark

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :
DAISABURO TAKASHIMA ET AL : EXAMINER: DICKEY, T. L.
SERIAL NO: 09/340,720 :
FILED: JUNE 29, 1999 : GROUP ART UNIT: 2826
FOR: SEMICONDUCTOR DEVICE

TECHNOLOGY CENTER 2800

RECEIVED
AUG - 6 2002

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

In response to the Official Action mailed May 6, 2002, please amend this application
as follows:

IN THE CLAIMS

Please amend Claims 1, 9 and 10 to read as follows:¹

1. (Twice Amended) A semiconductor device comprising:
a channel of a first conductivity type formed on a surface layer of a semiconductor
substrate;
a source and a drain of a second conductivity type formed on both sides of the
channel;

¹A marked-up copy of the changes made to the claims is attached.

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